

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H868C-CDMA BC0-RC3 SO55-777CH

DUT: H868C; Type: cdma2000 Digital Mobile Phone; Horizon; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 848.31 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 100.4 V/m; Power Drift = 0.04 dB

PMF = 1.050 is applied.

E-field emissions = 83.02 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

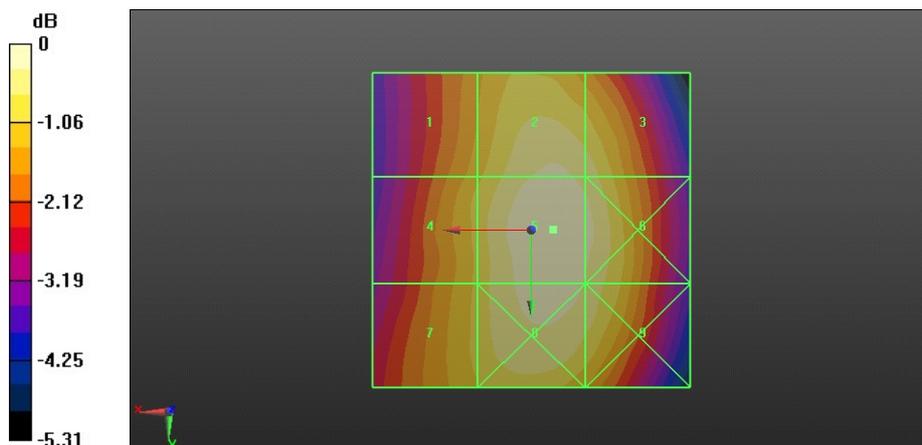
| | | |
|------------------------|------------------------|------------------------|
| Grid 1 M4 72.64 V/m | Grid 2 M4 80.53 V/m | Grid 3 M4 78.63 V/m |
| Grid 4 M4 74.64 V/m | Grid 5 M4 83.02 V/m | Grid 6 M4 80.93 V/m |
| Grid 7 M4 74.50 V/m | Grid 8 M4 81.56 V/m | Grid 9 M4 79.41 V/m |

Cursor:

Total = 83.02 V/m

E Category: M4

Location: -3.5, 0, 8.7 mm



0 dB = 83.02 V/m = 38.38 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H868C-CDMA BC0-RC3 SO55-384CH

DUT: H868C; Type: cdma2000 Digital Mobile Phone; Horizon; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 836.52 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 96.74 V/m; Power Drift = -0.11 dB

PMF = 1.050 is applied.

E-field emissions = 78.87 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

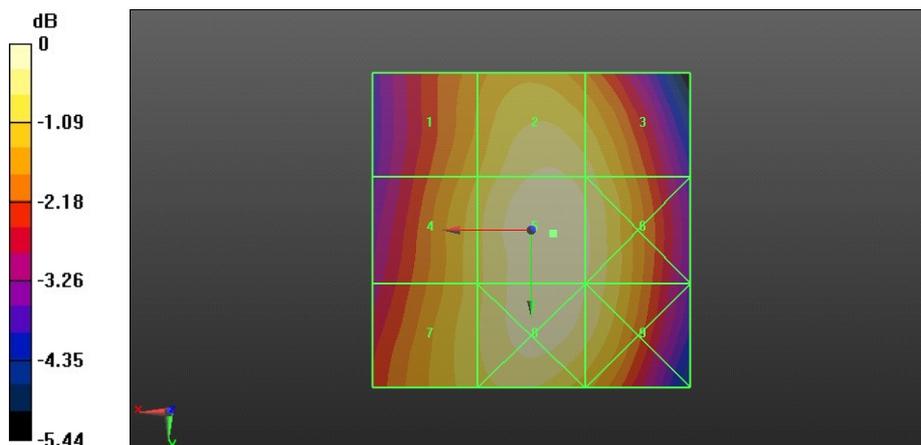
| | | |
|------------------------|------------------------|------------------------|
| Grid 1 M4 69.54 V/m | Grid 2 M4 76.35 V/m | Grid 3 M4 74.13 V/m |
| Grid 4 M4 71.85 V/m | Grid 5 M4 78.87 V/m | Grid 6 M4 76.41 V/m |
| Grid 7 M4 72.30 V/m | Grid 8 M4 78.20 V/m | Grid 9 M4 75.77 V/m |

Cursor:

Total = 78.87 V/m

E Category: M4

Location: -3.5, 0.5, 8.7 mm



0 dB = 78.87 V/m = 37.94 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H868C-CDMA BC0-RC3 SO55-1013CH

DUT: H868C; Type: cdma2000 Digital Mobile Phone; Horizon; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 824.7 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 86.86 V/m; Power Drift = -0.07 dB

PMF = 1.050 is applied.

E-field emissions = 70.67 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

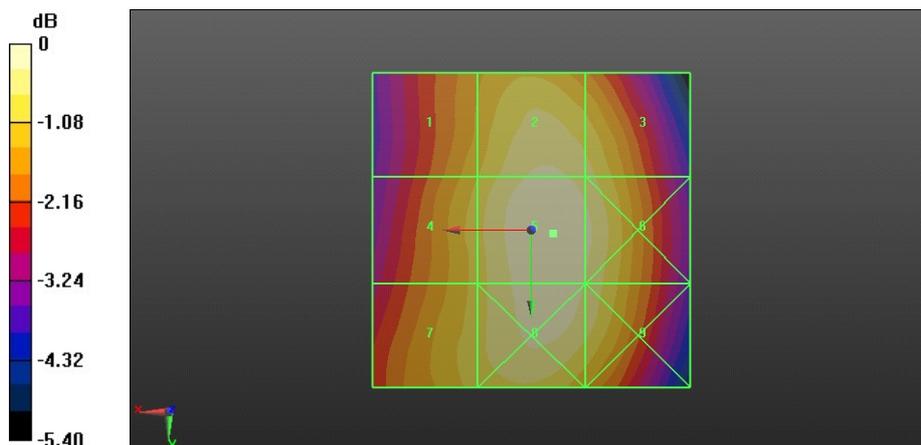
| | | |
|-------------------------------|-------------------------------|-------------------------------|
| Grid 1 M4 62.32 V/m | Grid 2 M4 68.50 V/m | Grid 3 M4 66.37 V/m |
| Grid 4 M4 64.21 V/m | Grid 5 M4 70.67 V/m | Grid 6 M4 68.70 V/m |
| Grid 7 M4 64.29 V/m | Grid 8 M4 69.69 V/m | Grid 9 M4 67.64 V/m |

Cursor:

Total = 70.67 V/m

E Category: M4

Location: -3.5, 0.5, 8.7 mm



0 dB = 70.67 V/m = 36.99 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H868C-CDMA BC1-RC3 SO55-1175CH

DUT: H868C; Type: cdma2000 Digital Mobile Phone; Horizon; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 1908.75 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 29.21 V/m; Power Drift = -0.01 dB

PMF = 1.020 is applied.

E-field emissions = 26.08 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

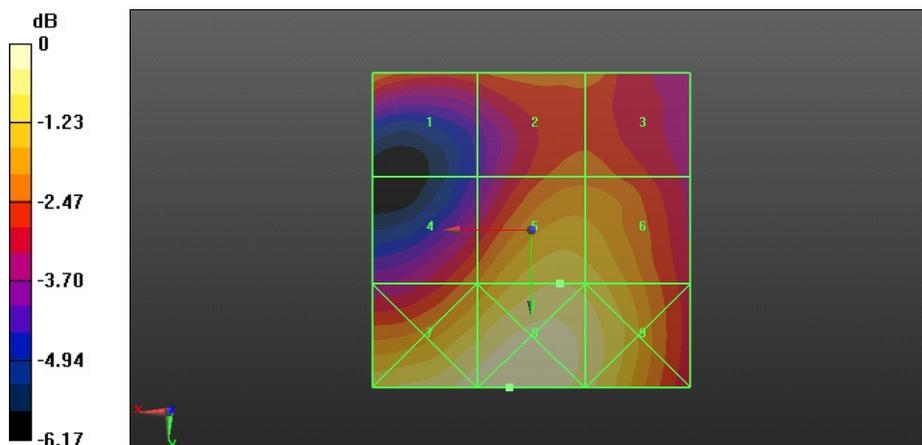
| | | |
|------------------------|------------------------|------------------------|
| Grid 1 M4 22.90 V/m | Grid 2 M4 22.23 V/m | Grid 3 M4 22.23 V/m |
| Grid 4 M4 22.67 V/m | Grid 5 M4 26.08 V/m | Grid 6 M4 25.63 V/m |
| Grid 7 M4 28.09 V/m | Grid 8 M4 28.64 V/m | Grid 9 M4 27.04 V/m |

Cursor:

Total = 28.64 V/m

E Category: M4

Location: 3.5, 25, 8.7 mm



0 dB = 28.64 V/m = 29.14 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H868C-CDMA BC1-RC3 SO55-600CH**DUT: H868C; Type: cdma2000 Digital Mobile Phone; Horizon; Serial: SAR1**

Communication System: HW-CDMA 2000; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 26.66 V/m; Power Drift = 0.00 dB

PMF = 1.020 is applied.

E-field emissions = 24.07 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

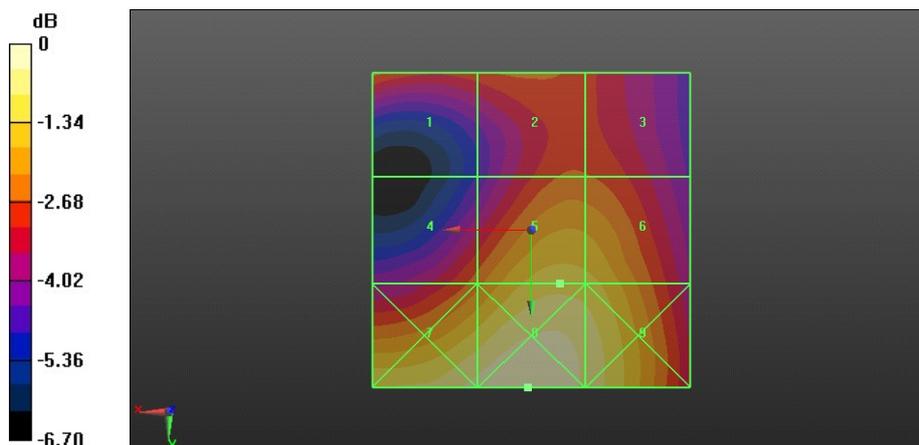
| | | |
|------------------------|------------------------|------------------------|
| Grid 1 M4 20.53 V/m | Grid 2 M4 20.19 V/m | Grid 3 M4 20.04 V/m |
| Grid 4 M4 20.60 V/m | Grid 5 M4 24.07 V/m | Grid 6 M4 23.80 V/m |
| Grid 7 M4 26.22 V/m | Grid 8 M4 27.12 V/m | Grid 9 M4 25.53 V/m |

Cursor:

Total = 27.12 V/m

E Category: M4

Location: 0.5, 25, 8.7 mm



0 dB = 27.12 V/m = 28.67 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H868C-CDMA BC1-RC3 SO55-25CH

DUT: H868C; Type: cdma2000 Digital Mobile Phone; Horizon; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 1851.25 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 26.82 V/m; Power Drift = 0.16 dB

PMF = 1.020 is applied.

E-field emissions = 25.02 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

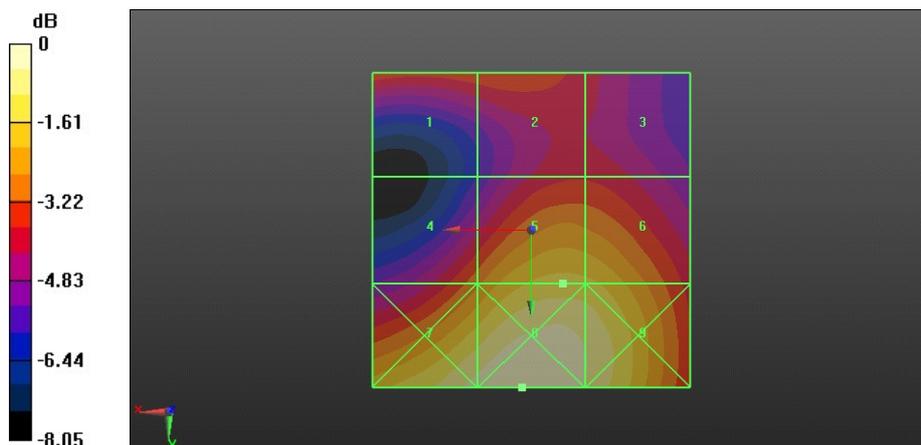
| | | |
|------------------------|------------------------|------------------------|
| Grid 1 M4 20.24 V/m | Grid 2 M4 20.30 V/m | Grid 3 M4 18.86 V/m |
| Grid 4 M4 21.20 V/m | Grid 5 M4 25.02 V/m | Grid 6 M4 24.82 V/m |
| Grid 7 M4 28.23 V/m | Grid 8 M4 29.27 V/m | Grid 9 M4 27.62 V/m |

Cursor:

Total = 29.27 V/m

E Category: M4

Location: 1.5, 25, 8.7 mm



0 dB = 29.27 V/m = 29.33 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H868C-CDMA BC0-RC3 SO55-777CH

DUT: H868C; Type: cdma2000 Digital Mobile Phone; Horizon; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 848.31 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08600 A/m; Power Drift = -0.00 dB

PMF = 0.9900 is applied.

H-field emissions = 0.1146 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

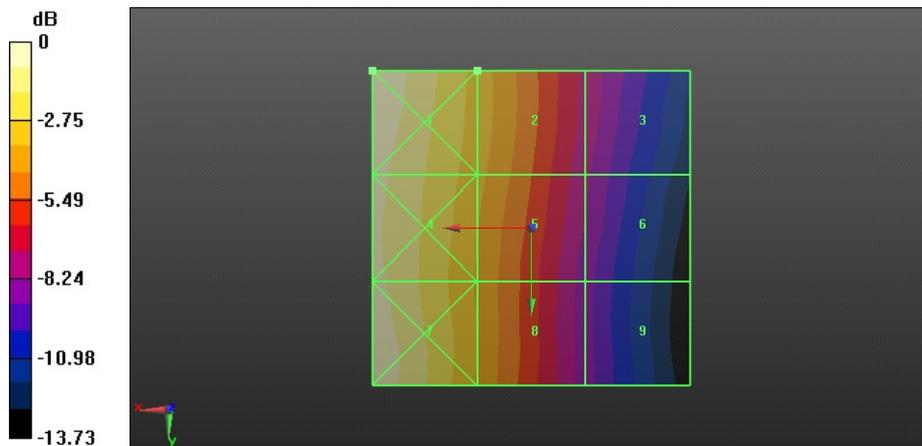
| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M4 0.163 A/m | Grid 2 M4 0.115 A/m | Grid 3 M4 0.069 A/m |
| Grid 4 M4 0.154 A/m | Grid 5 M4 0.111 A/m | Grid 6 M4 0.065 A/m |
| Grid 7 M4 0.160 A/m | Grid 8 M4 0.107 A/m | Grid 9 M4 0.060 A/m |

Cursor:

Total = 0.1634 A/m

H Category: M4

Location: 25, -25, 8.7 mm



0 dB = 0.1634 A/m = -15.73 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H868C-CDMA BC0-RC3 SO55-384CH

DUT: H868C; Type: cdma2000 Digital Mobile Phone; Horizon; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 836.52 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08100 A/m; Power Drift = -0.01 dB

PMF = 0.9900 is applied.

H-field emissions = 0.1107 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

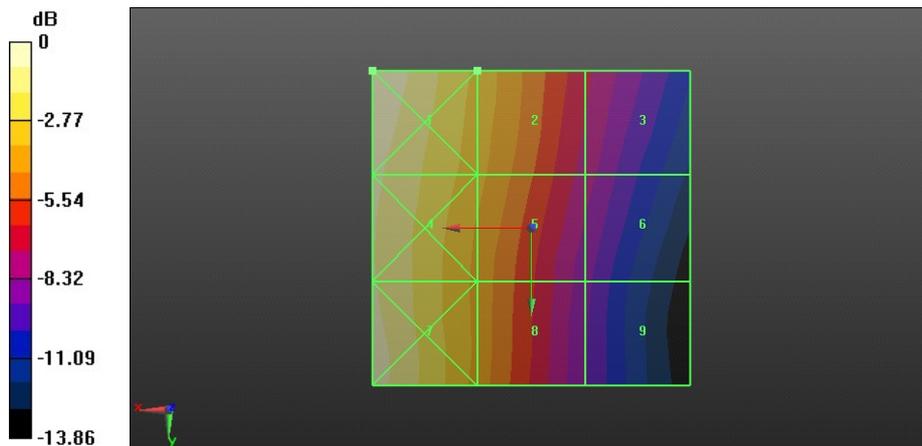
| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M4 0.156 A/m | Grid 2 M4 0.111 A/m | Grid 3 M4 0.069 A/m |
| Grid 4 M4 0.144 A/m | Grid 5 M4 0.106 A/m | Grid 6 M4 0.064 A/m |
| Grid 7 M4 0.149 A/m | Grid 8 M4 0.099 A/m | Grid 9 M4 0.056 A/m |

Cursor:

Total = 0.1561 A/m

H Category: M4

Location: 25, -25, 8.7 mm



0 dB = 0.1561 A/m = -16.13 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H868C-CDMA BC0-RC3 SO55-1013CH

DUT: H868C; Type: cdma2000 Digital Mobile Phone; Horizon; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 824.7 MHz; Duty Cycle: 1:1
 Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
 Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

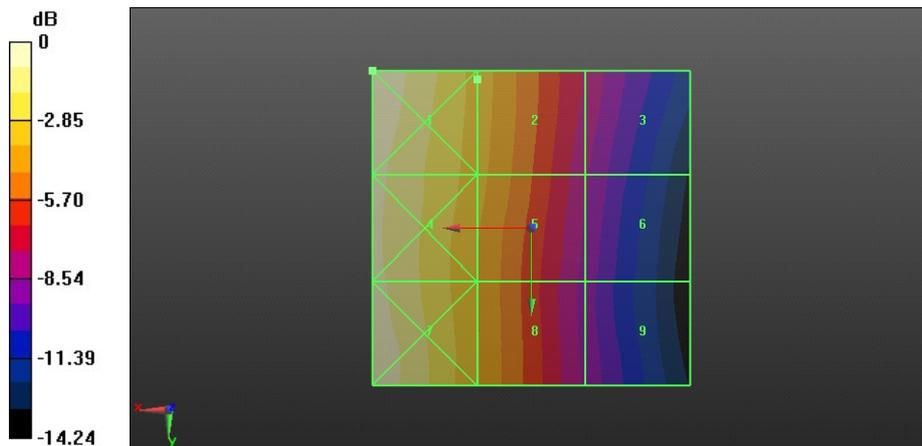
Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 0.07000 A/m; Power Drift = -0.02 dB
 PMF = 0.9900 is applied.
 H-field emissions = 0.09237 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M4 0.134 A/m | Grid 2 M4 0.092 A/m | Grid 3 M4 0.055 A/m |
| Grid 4 M4 0.125 A/m | Grid 5 M4 0.090 A/m | Grid 6 M4 0.051 A/m |
| Grid 7 M4 0.132 A/m | Grid 8 M4 0.088 A/m | Grid 9 M4 0.049 A/m |

Cursor:
 Total = 0.1338 A/m
 H Category: M4
 Location: 25, -25, 8.7 mm



0 dB = 0.1338 A/m = -17.47 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H868C-CDMA BC1-RC3 SO55-1175CH

DUT: H868C; Type: cdma2000 Digital Mobile Phone; Horizon; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 1908.75 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06400 A/m; Power Drift = -0.03 dB

PMF = 0.9400 is applied.

H-field emissions = 0.07849 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

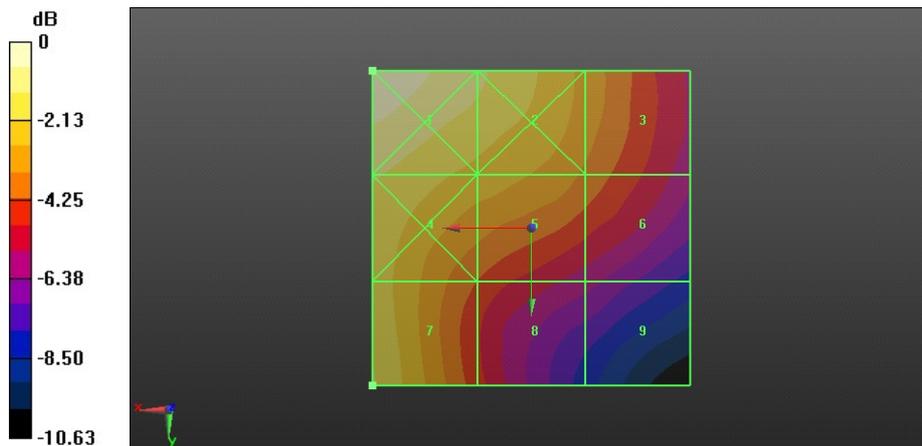
| | | |
|-------------------------------|-------------------------------|-------------------------------|
| Grid 1 M4 0.091 A/m | Grid 2 M4 0.079 A/m | Grid 3 M4 0.064 A/m |
| Grid 4 M4 0.078 A/m | Grid 5 M4 0.070 A/m | Grid 6 M4 0.060 A/m |
| Grid 7 M4 0.078 A/m | Grid 8 M4 0.056 A/m | Grid 9 M4 0.045 A/m |

Cursor:

Total = 0.09130 A/m

H Category: M4

Location: 25, -25, 8.7 mm



0 dB = 0.09130 A/m = -20.79 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H868C-CDMA BC1-RC3 SO55-600CH

DUT: H868C; Type: cdma2000 Digital Mobile Phone; Horizon; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06100 A/m; Power Drift = -0.05 dB

PMF = 0.9400 is applied.

H-field emissions = 0.06657 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

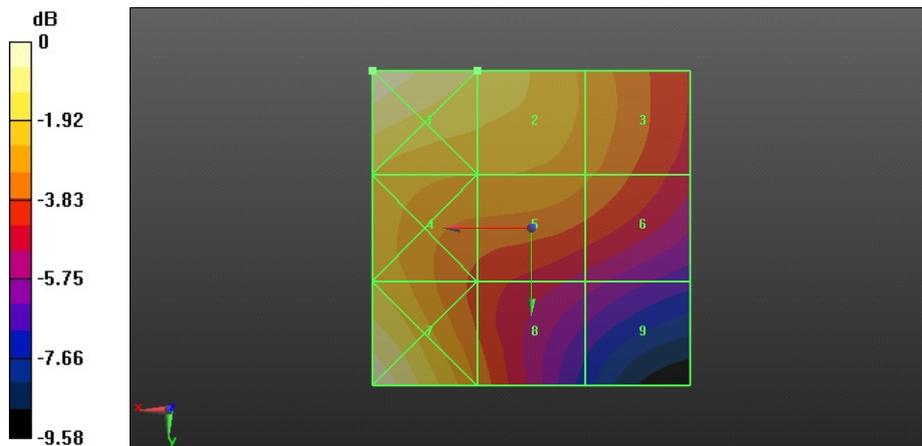
| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M4 0.077 A/m | Grid 2 M4 0.067 A/m | Grid 3 M4 0.057 A/m |
| Grid 4 M4 0.063 A/m | Grid 5 M4 0.058 A/m | Grid 6 M4 0.054 A/m |
| Grid 7 M4 0.076 A/m | Grid 8 M4 0.053 A/m | Grid 9 M4 0.042 A/m |

Cursor:

Total = 0.07738 A/m

H Category: M4

Location: 25, -25, 8.7 mm



0 dB = 0.07738 A/m = -22.23 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H868C-CDMA BC1-RC3 SO55-25CH

DUT: H868C; Type: cdma2000 Digital Mobile Phone; Horizon; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 1851.25 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06600 A/m; Power Drift = 0.01 dB

PMF = 0.9400 is applied.

H-field emissions = 0.06615 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

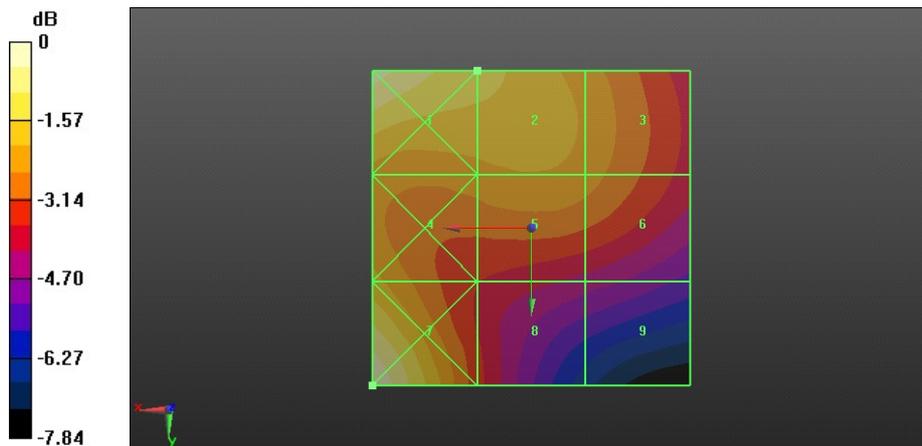
| | | |
|--------------------------------------|--------------------------------------|--------------------------------------|
| Grid 1 M4 0.075 A/m | Grid 2 M4 0.066 A/m | Grid 3 M4 0.060 A/m |
| Grid 4 M4 0.062 A/m | Grid 5 M4 0.061 A/m | Grid 6 M4 0.059 A/m |
| Grid 7 M4 0.077 A/m | Grid 8 M4 0.052 A/m | Grid 9 M4 0.047 A/m |

Cursor:

Total = 0.07720 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.07720 A/m = -22.25 dBA/m